



6.4-7.2GHz, 50W, 50V GaN fully matched PA Module

Description

The SMAV6472-50 is a 50-watt, integrated 2-stage Power Amplifier Module, designed for 5.5G or pre-6G massive MIMO applications, with frequencies from 6.4 to 7.2 GHz. The module is 50 Ω input and output fully matched, and requires minimal external components. The module offers a much smaller footprint than traditional discrete component solutions, with much less sensitivity for production, housed in 10*6mm cost effective plastic open cavity package.

The module incorporates a Doherty circuit delivering high power added efficiency for the entire module at 8W average power.

Innegration owns the patents for internal Doherty architecture, and related plastic open cavity.

• Typical Performance of Doherty Demo (On Innegration fixture with device soldered):

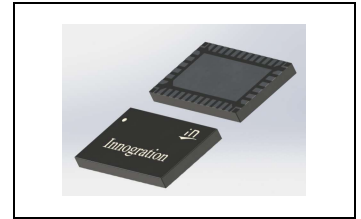
$V_{DS}=50V, I_{dq1}=15mA, I_{dq2}=65mA, V_{peak}=-6.2V$				
$P_{out}=39dBm$				
Freq (MHz)	Pin(dBm)	Gain (dB)	EFF (%)	ACPR (dBc)
6400	16.06	22.9	30.2	-30.2
6500	14.75	24.3	31.7	-32.5
6600	14.63	24.4	33.0	-34.8
6700	14.86	24.1	33.3	-36.4
6800	15.03	24.0	33.3	-39.0
6900	15.82	23.2	31.5	-40.2
7000	16.43	22.6	30.2	-37.2
7100	16.42	22.6	30.2	-33.4
7200	16.00	23.0	30.3	-30.8

• Notes:

(1) WCDMA signal: 3GPP test model 1; 1 to 64 DPCH; Channel Bandwidth=3.84MHz, PAR =10.5 dB at 0.01 % probability on CCDF.

Features

- Industry leading RF performance for 5.5G or pre-6G MIMO AAU, for instance
 - ✓ 32T or 64T
- Plastic open cavity without molding compound brings advantage compared to molded design
 - ✓ Minimize the risk of high density thermal distribution in fanless system for longer life time
 - ✓ Highly consistent RF performance for yield of volume production
- 50 Ω Input/output matched,
- Integrated Doherty Final and driver Stage
- 6x10 mm Surface Mount Package, full copper flange underneath for grounding and heat dissipation



**Pin Configuration and Description**

Pin No.	Symbol	Description
1	VD1	Driver Amplifier, Drain Bias
3	VG1	Driver Amplifier, Gate Bias
6	RF IN	RF Input
11	VG3	Carrier Amplifier, Gate Bias
16	BE	VBW Enhance
22	RF OUT	RF Output
27	VD2	Peaking Amplifier, Drain Bias
32	VG2	Peaking Amplifier, Gate Bias
4,8-10,14-15,17,19,21,24,26,28,29,33-35	NC	No connection
2,5,7,12,13,18,20,23,25,30,31,36	GND	Internal Grounding, recommend connecting to Epad ground
Package Base	GND	DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DS}	200	Vdc
Gate--Source Voltage	V_{GS}	-8 to +0.6	Vdc
Operating Voltage	V_{DD}	+55	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_c	+150	°C
Operating Junction Temperature	T_J	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance@Average Power, Junction to Case $T_{case}=+85^{\circ}\text{C}$, CW Test, $P_{out}=8\text{W}$,	$R_{\theta JC}$	4.3	°C/W

Notes:

- (1) The thermal resistance is acquired by our company's FEA model, which was calibrated by IR measurement, the value shall be applied to reliability.
- (2) The reference T_{case} temperature 85°C is apply on the backside of package.
- (3) If the device soldering onto the 20mil Rogers PCB with $50 \times \Phi 0.4\text{mm}$ via hole beneath the package backside and the reference temperature T_{case} (85°C) apply on the groundside of the PCB, the total thermal resistance $R_{\theta JC}$ (TBD) °C/W.
- (4) The power dissipation in the table is overall dissipation which include Carrier PA, Peaking PA and driver PA.

Table 3. ESD Protection Characteristics

Test Methodology	Class Voltage
Human Body Model(HBM) (JEDEC Standard JESD-A114)	TBD



Charged Device Model (CDM) (JEDEC Standard JESD22-C101F)

TBD

Table 4. Electrical Characteristics

Parameter	Condition	Min	Typ	Max	Unit
Frequency Range		6.4		7.2	GHz
Carrier Quiescent Current (I_{DQ})			65		mA
Peak PA Gate Quiescent Voltage (V_{PEAK})			06.2		V
Power Gain @ P1dB	Freq=7.2GHz		20		dB
P3dB	Freq=7.2GHz		47		dBm
Drain Efficiency@ P3dB	Freq=7.2GHz		45		%

Unless otherwise noted: $T_A = 25^{\circ}\text{C}$, $V_D = 50\text{ V}$, Pulse Width=20 us, Duty cycle=10%

Load Mismatch of per Section (On Test Fixture, 50 ohm system): $f = 7.2\text{ GHz}$

VSWR 10:1 at P3dB pulse CW Output Power

No Device Degradation

TYPICAL CHARACTERISTICS

Figure 1. Power Gain and Drain Efficiency as Function of Pulsed CW Output Power @VDS=50V

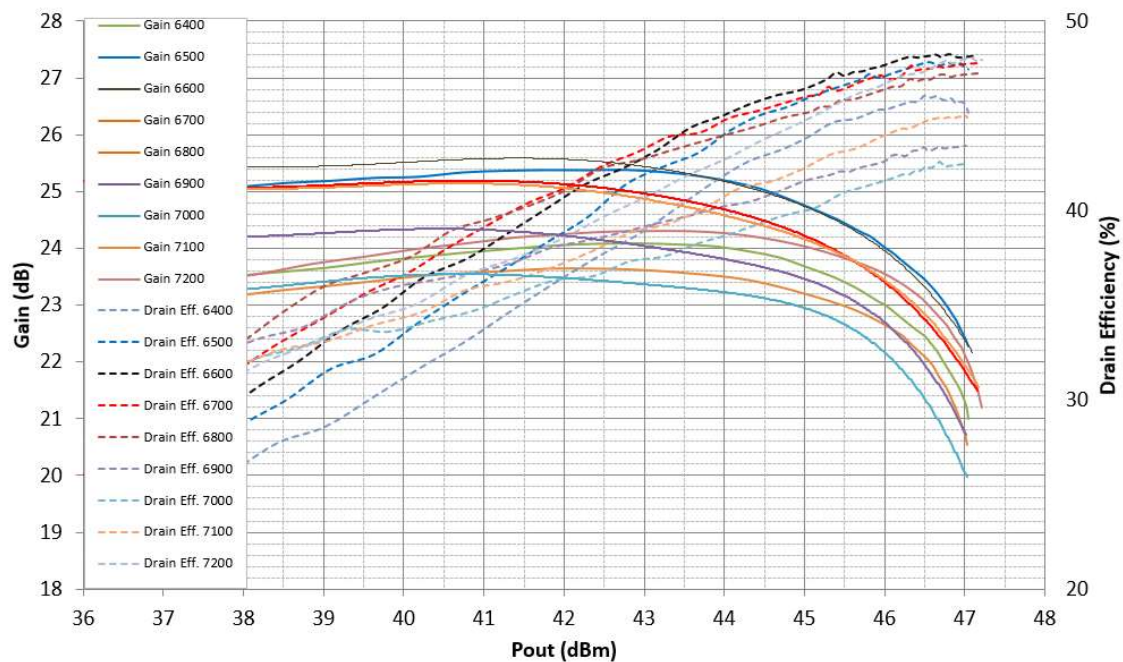


Figure 2. Network analyzer output S11/S21

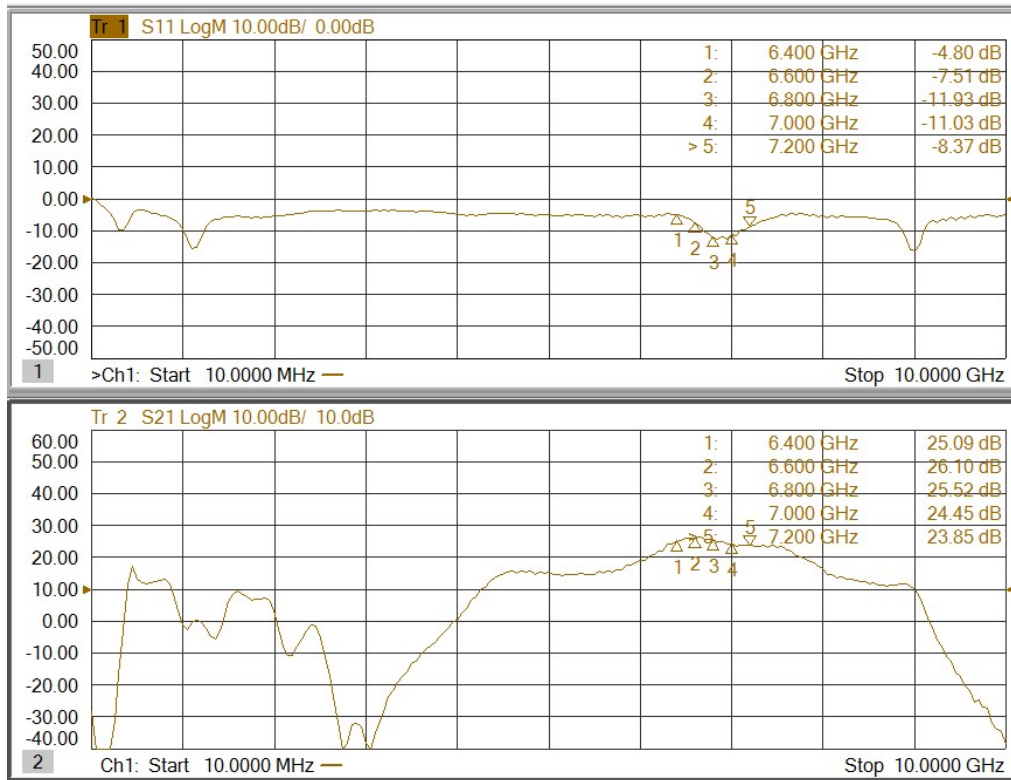


Figure 3: Picture of application board Doherty circuit

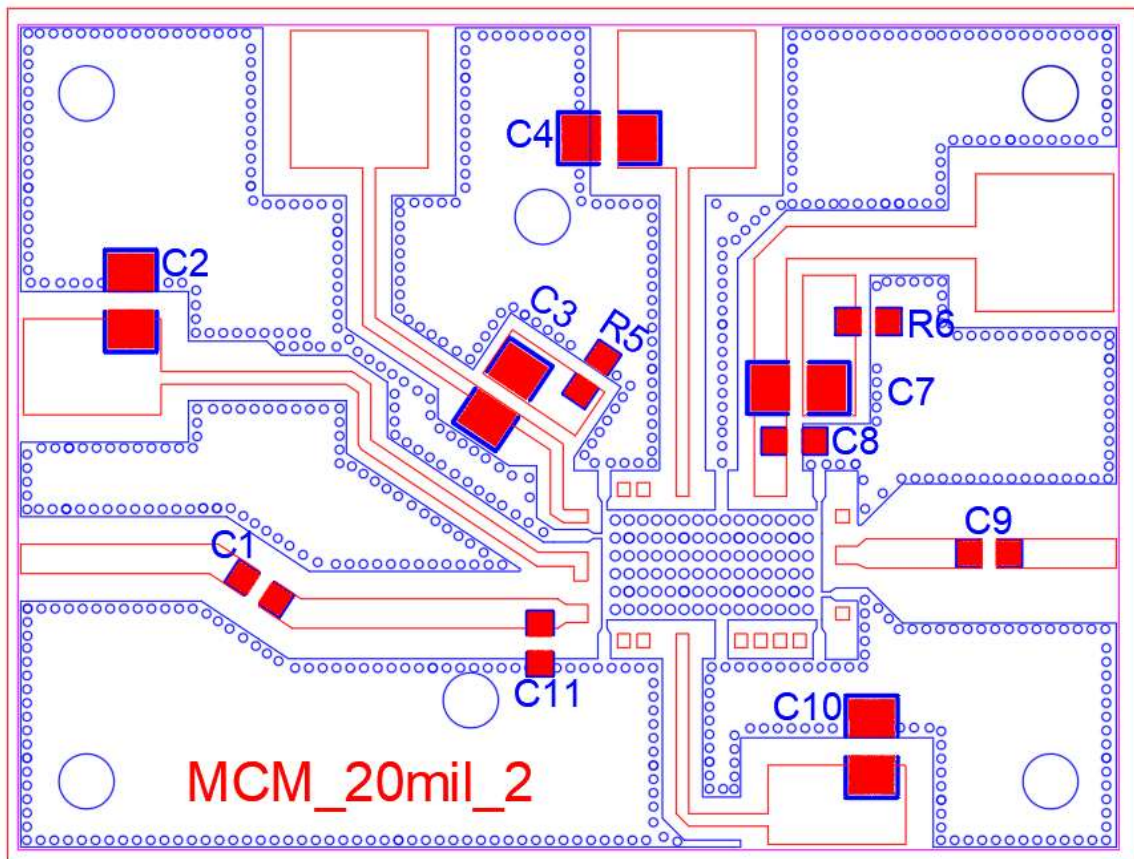




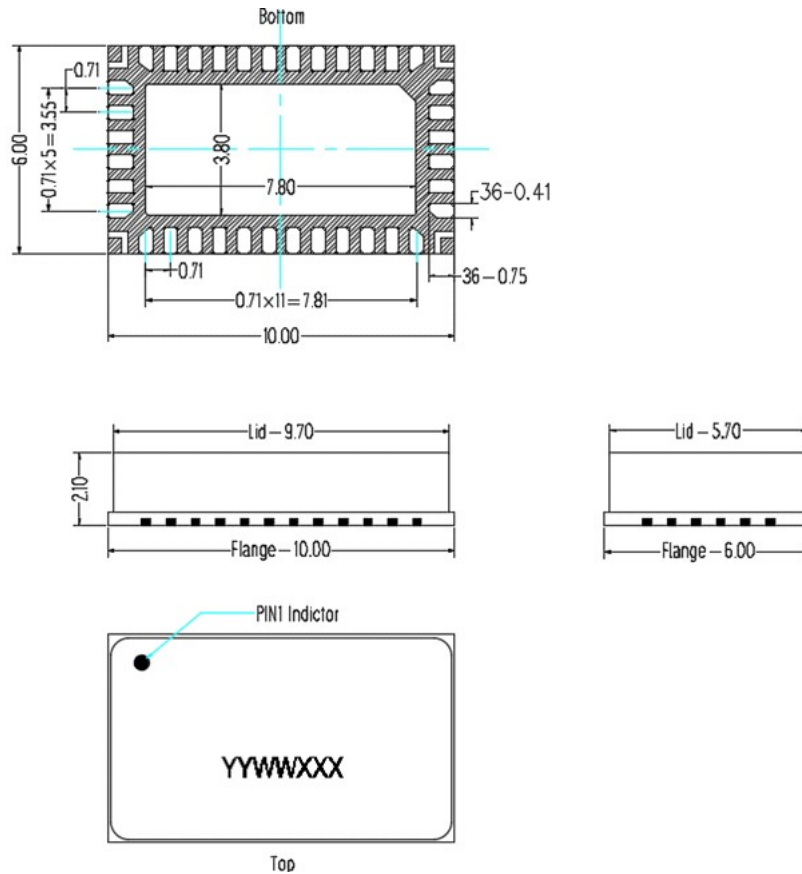
Table 4. Bill of materials of application board (PCB layout upon request, RO4350B 20mils)

Component	Value	Description
U1	SMAV6472_50	PA Module
C1、C8、C9	3.9pF	ATC600S
C2、C3、C4、C7	10uF	TDK1206
C11	2.0pF	ATC600S
R5,R6	10 Ω	Unimo0603



Package Dimensions

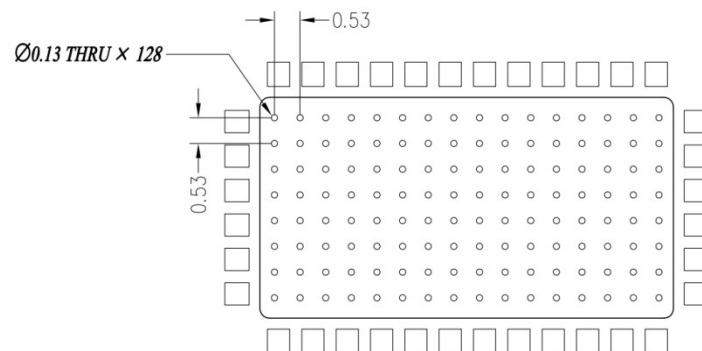
10*6 Plastic Package



Notes:

1. All dimensions are in mm;
2. The tolerances unless specified are ± 0.2 mm.

Mounting Footprint Pattern



Notes:

1. All dimensions are in mm;
2. Vias are required under the backside paddle of this device for proper RF/DC grounding and thermal dissipation. ALL vias are PTH to ground.



Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2024/6/24	Rev 1.0	Preliminary Datasheet

Application data based on HJ-24-12

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